

Quantum weight

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We introduce the concept of quantum weight as a fundamental property of quantum many-body systems that is encoded in the ground-state static structure factor and characterizes density fluctuation at long wavelength. We show that quantum weight of three-dimensional electron systems is related by a sum rule to the inverse dielectric function, which describes electron energy loss spectrum. Using this relation, we derive an upper and a lower bound on the quantum weight of real materials in terms of their electron density, static dielectric constant, and plasmon energy. For systems with short-range interactions or Coulomb systems in reduced dimensions, we derive a sum rule relating the quantum weight to the optical conductivity and establish a remarkable connection with the quantum geometry of many-body ground states. Our work highlights quantum weight as a key material parameter that can be experimentally determined.

The ground state wavefunction of quantum states of matter encodes a wealth of information about their thermodynamic and transport properties. Ground-state correlation functions reveal the emergence of long-range order. The topology of the ground state distinguishes topologically distinct phases of insulators and determines the quantization of physical properties such as the Hall conductivity [1, 2].

In this work, we introduce a ground state property of quantum many-body systems that governs density fluctuation at long wavelength, which we call quantum weight. The quantum weight is defined with the ground-state static structure factor at small wavevector. We derive a sum rule that relates the quantum weight of three-dimensional (3D) Coulomb systems to the dynamical density response described by the imaginary part of the inverse dielectric function $\text{Im}[1/\epsilon(\omega)]$, which is called energy loss function. Using this relation, we find upper and lower bounds on the quantum weight of real materials based on their plasmon energy, static dielectric constant and electron density. These bounds are shown to be remarkably tight for a variety of semiconductors and insulators.

For systems with short-range interaction or Coulomb systems of reduced dimensions, the long-wavelength density response is directly related to the conductivity $\sigma(\mathbf{q}, \omega)$ at $\mathbf{q} \rightarrow 0$ through the continuity relation. This allows us to derive a sum rule for gapped systems that relates the quantum weight to optical conductivity. Our work establishes the quantum weight as an important ground state property and a powerful tool for studying electronic structure and dynamical response of solids.

We also discuss the connection between quantum weight and quantum metric [3]. In a seminal work, Souza, Wilkins and Martin (SWM) found a sum rule that relates optical conductivity $\sigma(\omega)$ to the many-body quantum metric that describes the response of the ground state wavefunction to twisted boundary condition [4]. By combining the SWM sum rule and our sum rule, we conclude that despite being conceptually distinct, the many-body

quantum metric and the quantum weight are equal (up to a factor of 2π) in many-body systems with an energy gap, provided that inter-particle interaction is not too long-ranged. For 3D Coulomb systems such as real solids, however, we show explicitly that these two quantities are unequal, because charge fluctuation and therefore the quantum weight are strongly affected by Coulomb screening. Related discussions can be found in Ref. [5, 6].

Quantum weight.—To motivate the concept of quantum weight, let us start with interacting electrons in a deep periodic potential. The classical ground state at $\hbar = 0$ is simply a lattice of electron point particles located at the periodic potential minima. Once electron's kinetic energy is taken into account, there will be quantum fluctuation in electron's position due to the Heisenberg uncertainty principle, which makes the quantum ground state different from the classical one.

In general, in order to quantify the amount of position fluctuation in a many-particle system at zero temperature, we consider the static structure factor which measures equal-time density-density correlation in the ground state: $S_{\mathbf{q}} \equiv (1/V) \langle \hat{n}_{\mathbf{q}} \hat{n}_{-\mathbf{q}} \rangle$. For a periodic system, the static structure factor in the classical limit is composed of δ functions located at reciprocal lattice vectors only. Therefore, $S_{\mathbf{q}}$ at any other wavevector can be nonzero only because of quantum uncertainty in particle position. We shall focus on the leading order behavior of $S_{\mathbf{q}}$ at small finite \mathbf{q} , which describes long-wavelength quantum fluctuations.

This work considers quantum many-body systems in which $S_{\mathbf{q}}$ is proportional to q^2 at small wavevector:

$$S_{\mathbf{q}} = \frac{1}{2\pi} K_{\alpha\beta} q_{\alpha} q_{\beta} + \dots, \quad (1)$$

with $\hat{n}_{\mathbf{q}} = \int d\mathbf{r} e^{-i\mathbf{q}\cdot\mathbf{r}} \hat{n}(\mathbf{r})$ the number density operator with wavevector \mathbf{q} and V the volume of the system. As we shall show later, the q^2 behavior of static structure factor occurs ubiquitously in insulators and in 3D metals with long-range Coulomb interaction. We call the quadratic coefficient K defined by Eq. (1) *quantum weight*. K has

the unit of length to the power of $2 - d$, where d is the spatial dimension of the system.

To gain intuition about the quantum weight, let us consider a 3D electron system where Coulomb interaction and periodic potential dominate over the kinetic energy, leading to a lattice of strongly localized electrons. When the kinetic energy is treated perturbatively around the classical limit, the long-wavelength fluctuations can be described in terms of the displacement from the mean position of electrons. For the simplest case of one electron per unit cell (a Wigner solid), the effective Lagrangian takes the following form [6]:

$$\mathcal{L} = \sum_{\mathbf{q}} \frac{m}{2} \left(|\dot{\mathbf{u}}_{\mathbf{q}}|^2 - (\omega_0^2 + \omega_p^2 \frac{q_\alpha q_\beta}{q^2}) u_{\mathbf{q}\alpha} u_{-\mathbf{q}\beta} \right), \quad (2)$$

where $u_{\mathbf{q}}$ is the Fourier transform of the displacement of electrons, ω_0 represents the pinning of electron lattice by the potential, and the last term with the bare plasma frequency $\omega_p \equiv (ne^2/(\epsilon_0 m))^{1/2}$ describes the change in Coulomb energy due to the charge density from the displacement of electrons: $\rho = -e\nabla \cdot \mathbf{u}$. n, m are the electron density and the free electron mass, respectively.

The low-energy spectrum of this system consists of a longitudinal mode $\mathbf{u}_{\mathbf{q}}^L \parallel \mathbf{q}$ and two transverse modes ($\mathbf{u}_{\mathbf{q}}^T \perp \mathbf{q}$). Importantly, the dispersion relations of longitudinal and transverse modes differ because the longitudinal mode represents the plasma oscillation involving electron density fluctuation, which costs Coulomb energy even at $\mathbf{q} \rightarrow 0$ limit due to the long-range nature of Coulomb force. Indeed, it is clear from Eq. (27) that the frequency of the transverse mode is $\omega_T = \omega_0$, while that of the longitudinal mode is $\omega_L = \sqrt{\omega_0^2 + \omega_p^2} > \omega_T$. $\hbar\omega_L$ is the real plasmon energy of the system, which is larger than $\hbar\omega_p$ due to the presence of periodic potential.

We now explicitly calculate the quantum weight for this system by quantizing the Lagrangian (2) (see Supplemental Materials for details). The static structure factor at small \mathbf{q} , $S_{\mathbf{q}} = \frac{1}{V} \langle \hat{n}_{\mathbf{q}} \hat{n}_{-\mathbf{q}} \rangle$, is given by zero-point fluctuation in the displacement field \mathbf{u} ,

$$S_{\mathbf{q}} = n \langle (\mathbf{q} \cdot \mathbf{u}_{\mathbf{q}})(\mathbf{q} \cdot \mathbf{u}_{-\mathbf{q}}) \rangle, \text{ for } \mathbf{q} \rightarrow 0. \quad (3)$$

Importantly, only the longitudinal mode ($\mathbf{u}_{\mathbf{q}}^L \parallel \mathbf{q}$) contributes to $S_{\mathbf{q}}$. From the amplitude fluctuation of the harmonic oscillator $\langle |\mathbf{u}_{\mathbf{q}}^L|^2 \rangle = \hbar/(2m\omega_L)$, we find the quantum weight as

$$K = \frac{\pi n \hbar}{m\omega_L} = \frac{\pi \hbar \epsilon_0 \omega_p^2}{e^2 \omega_L}. \quad (4)$$

For a given electron density, as the potential depth decreases, ω_0 and therefore ω_L become smaller, leading to an increase of quantum weight, consistent with electrons being less localized and therefore more quantum.

In the following, we will study the properties of quantum weight in general systems with Coulomb or short-range interactions, and reveal its relations to dynamical

density response, optical conductivity, and many-body quantum metric.

Sum rule relating complex dielectric function to quantum weight.— First, we show a sum rule that directly relates the quantum weight of 3D Coulomb systems to the inverse dielectric function. Let us consider the density response of a solid to an external potential V_{ext} with wavevector \mathbf{q} and frequency ω . The induced change in the density is characterized by the density-density response function $\Pi(\mathbf{q}, \omega)$: $\rho(\mathbf{q}, \omega) = \Pi(\mathbf{q}, \omega) V_{\text{ext}}(\mathbf{q}, \omega)$. By the fluctuation-dissipation theorem [7], $\text{Im} \Pi(\mathbf{q}, \omega)$ is directly related to the dynamical structure factor: $-\text{Im} \Pi(\mathbf{q}, \omega) = e^2 S(\mathbf{q}, \omega)/(2\hbar)$, where the dynamical structural factor is defined as $S(\mathbf{q}, \omega) = (1/V) \int_{-\infty}^{\infty} dt e^{i\omega t} \langle \hat{n}_{\mathbf{q}}(t) \hat{n}_{-\mathbf{q}}(0) \rangle$. Integrating this equality over frequencies yields a sum rule that relates the quantum density response to the static structure factor:

$$-\int_0^{\infty} d\omega \text{Im} \Pi(\mathbf{q}, \omega) = \frac{\pi e^2}{\hbar} S_{\mathbf{q}}, \quad (5)$$

where we have used $S(\mathbf{q}, \omega) = 0$ for $\omega < 0$ at zero temperature.

The density response function defines the dielectric constant ϵ which relates the *external* charge density ρ_{ext} to the *total* (or screened) charge density ρ_{tot} as $\rho_{\text{ext}} = \epsilon \rho_{\text{tot}}$ (for the moment we assume the dielectric tensor is isotropic and present the general result later). The total charge is the sum of the external charge and the induced charge: $\rho_{\text{tot}} = \rho_{\text{ext}} + \Pi(\mathbf{q}) V(\mathbf{q}, \omega)$, where $V(\mathbf{q}, \omega) = U(\mathbf{q}) \rho_{\text{ext}}(\mathbf{q}, \omega)$ is the potential created by external charges, and $U(\mathbf{q})$ describes the interaction between two point charges. This leads to a relation between ϵ and Π :

$$\epsilon(\mathbf{q}, \omega) = (1 + U(\mathbf{q}) \Pi(\mathbf{q}, \omega))^{-1} \quad (6)$$

Combining Eq. (5) and (6), we obtain a general relation between the dielectric constant and ground state static structural factor:

$$\int_0^{\infty} d\omega \text{Im} \left[-\frac{1}{\epsilon(\mathbf{q}, \omega)} \right] = \frac{\pi e^2}{\hbar} U(\mathbf{q}) S_{\mathbf{q}}. \quad (7)$$

As a sum rule that relates the inverse dielectric function $1/\epsilon(\mathbf{q}, \omega)$ to the ground-state structure factor $S_{\mathbf{q}}$, Eq. (7) applies to general many-body systems.

For 3D systems with long-range Coulomb interaction, $U(\mathbf{q}) = 1/(\epsilon_0 q^2)$ is singular at $\mathbf{q} \rightarrow 0$, while, as we shall show later, the left hand side of Eq. (7) is finite. Therefore, the static structure factor is proportional to q^2 at small \mathbf{q} . Taking $\mathbf{q} \rightarrow 0$ limit of Eq. (7) then yields a sum rule that relates the quantum weight of 3D Coulomb systems to the inverse dielectric function:

$$\int_0^{\infty} d\omega \text{Im} \left[-\frac{1}{\epsilon_{\alpha\alpha}(\omega)} \right] = \frac{1}{2\hbar} \frac{e^2 K_{\alpha\alpha}}{\epsilon_0} \quad (8)$$

The integrand of the left-hand side of Eqs. (7) and (8) is called energy loss function and represents density excitations such as plasmon. It can be directly measured by the inelastic X-ray scattering or the electron energy loss spectroscopy. Therefore, the sum rule (8) provides a direct method of determining the quantum weight of real materials.

To illustrate the relation between quantum weight and dielectric function, consider the example of Wigner electron solid introduced earlier. Its dielectric function is given by [6]

$$\epsilon(\omega) = \frac{\omega_L^2 - (\omega + i\delta)^2}{\omega_T^2 - (\omega + i\delta)^2}. \quad (9)$$

where $\delta \rightarrow +0$ is understood. Note that the pole of $1/\epsilon$ corresponds to the longitudinal mode, while the pole of ϵ corresponds to the transverse mode. From the expressions for $\epsilon(\omega)$ and K , we can explicitly verify the sum rule (8).

In general, the expression for quantum weight in terms of electron density and a single plasmon frequency ω_L , Eq. (4), holds (approximately) in systems where the density response at long wavelength is (nearly) saturated by this single plasmon mode. Such single mode approximation was widely used in the study of liquid Helium [8] and fractional quantum Hall systems [9]. As our analysis has shown, this approximation is exact for Wigner solid in the semiclassical limit ($\hbar \rightarrow 0$). It is also exact in a Coulomb gas without external potential, which corresponds to the limit $\omega_0 \rightarrow 0$ in our discussion here. The quantum weight of 3D Coulomb gas, which we denote as K_p , is simply determined by the bare plasma frequency: $e^2 K_p / \epsilon_0 = \pi \hbar \omega_p$. More generally, within the single mode approximation, the quantum weight in dimensionless unit can be written compactly as: $K/K_p \approx \omega_p / \omega_L$.

Bounds on quantum weight.— Real materials are obviously more complicated than Wigner solid. The presence of core and valence electrons leads to multiple plasmon modes at different energies, hence the single mode approximation is not expected to work very well. In order to estimate the quantum weight of real materials, we now derive rigorous upper and lower bounds on this quantity based on its relation to the inverse dielectric function, Eq. (8). To this end, it is convenient to define the i -th moment of the energy loss function:

$$K_i \equiv \int_0^\infty d\omega \omega^i \text{Im} \left[-\frac{1}{\epsilon_{\alpha\alpha}(\omega)} \right] \quad (10)$$

In particular, we focus on K_0, K_{-1} , and K_1 . $K_0 = e^2 K / (2\hbar\epsilon_0)$ is simply the quantum weight up to a factor as seen from Eq. (8), while K_1 and K_{-1} are related to the bare plasma frequency and static dielectric constant

respectively:

$$K_1 = \frac{\pi\omega_p^2}{2}, \quad (11)$$

$$K_{-1} = \frac{\pi}{2}(1 - \epsilon_{\alpha\alpha}^{-1}(0)), \quad (12)$$

Eq. (11) is the f sum rule [10, 11], while Eq. (12) is a consequence of the Kramers-Kronig relation for $1/\epsilon$ which describes the density response [10, 12].

Bounds on the quantum weight can be obtained by exploring the inequality relations between K_{-1} , K_0 and K_1 . First, the Cauchy-Schwartz inequality, $\int_0^\infty |f(x)|^2 dx \int_0^\infty |g(x)|^2 dx \geq |\int_0^\infty f(x)g(x) dx|^2$, with $f(x) = \sqrt{\omega} \text{Im}[-\epsilon^{-1}]$, $g(x) = \sqrt{\omega^{-1} \text{Im}[-\epsilon^{-1}]}$, yields an upper bound on K_0 :

$$K_0 \leq \sqrt{K_1 K_{-1}}. \quad (13)$$

To find the lower bound on K_0 , note that the energy loss function $\text{Im}[-1/\epsilon(\omega)]$ describes the energy absorption by density excitations, hence $\text{Im}[-1/\epsilon(\omega)]$ is semi-positive and can be finite only when $\hbar\omega \geq E_g$. Here, E_g is the energy of the lowest density excitation which couples to a long-wavelength potential, i.e., the lowest plasmon energy. Therefore, a lower bound on K_0 is obtained by replacing ω in K_{-1} with E_g/\hbar :

$$K_0 \geq \frac{E_g}{\hbar} K_{-1}. \quad (14)$$

Combining Eqs. (13) and (14) with the sum rules (11) and (12), we obtain an upper and a lower bound on the quantum weight in terms of electron density, static dielectric constant and the plasmon energy,

$$\pi(1 - \epsilon^{-1})E_g \leq e^2 K / \epsilon_0 \leq \pi \sqrt{1 - \epsilon^{-1}} \hbar \omega_p. \quad (15)$$

It is important to note that the upper bound on K_0 given here is necessarily finite, because the static dielectric constant is always greater than 1. Returning to the discussion after Eq. (7), the boundedness of K_0 guarantees that the static structure factor of 3D Coulomb systems is indeed proportional to q^2 .

Remarkably, we find the bounds on the quantum weight (15) work very well for real materials. Using the electron density and the measured values of static electronic dielectric constant and plasmon energy, we calculated the upper and the lower bound on the quantum weight. The results are shown in Fig. 1. The most remarkable case is diamond, where the quantum weight is bounded as $0.49 \text{ \AA}^{-1} \leq K \leq 0.60 \text{ \AA}^{-1}$. The bounds also work well for cubic boron nitride (c-BN): $0.41 \text{ \AA}^{-1} \leq K \leq 0.57 \text{ \AA}^{-1}$. For all the materials we calculated, the upper bound is less than 1 \AA^{-1} . It is remarkable that the quantum weight of real materials lies within such a narrow range.

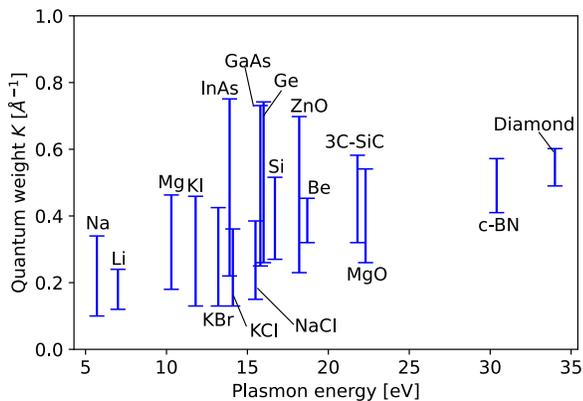


FIG. 1. The bounds on the quantum weight K for real materials. As the energy gap, we used the plasmon energy obtained from electron energy loss spectroscopy. The details of the used parameters are given in supplemental materials (also see Ref. [6]).

Quantum weight and optical conductivity.— Besides describing long-wavelength density fluctuation, the quantum weight is also closely related to the conductivity through the continuity equation for charge and current. To see this, we first relate the dynamical density response function $\Pi(\mathbf{q}, \omega)$ to the conductivity by the continuity equation: $-i\omega\rho + i\mathbf{q} \cdot \mathbf{j} = 0$. It is important to note that density fluctuation is accompanied by longitudinal current only, i.e., the current parallel to the wavevector $\mathbf{j}_L \parallel \mathbf{q}$. The conductivity for the longitudinal current σ^L is related to the density response function Π as

$$\Pi(\mathbf{q}, \omega) = -i \frac{q_\alpha q_\beta \sigma_{\alpha\beta}^L(\mathbf{q}, \omega)}{\omega \epsilon(\mathbf{q}, \omega)}. \quad (16)$$

Importantly, $\sigma^L(\mathbf{q}, \omega)$ is defined as the current \mathbf{j} induced by an *total* (or screened) electric field \mathbf{E}_{tot} parallel to the wavevector \mathbf{q} : $\mathbf{j}_\mathbf{q}(\omega) = \sigma^L(\mathbf{q}, \omega) \mathbf{E}_{\text{tot}}(\mathbf{q}, \omega)$. On the other hand, Π describes the response to the *external* potential. As the external field differs from the total electric field by the dielectric function: $\mathbf{E}_{\text{tot}} = \mathbf{E}_{\text{ext}}/\epsilon$, ϵ appears in the denominator in Eq. (16) to account for electric field screening by density fluctuation. Combining Eq. (16) with Eq. (5) and taking $\mathbf{q} \rightarrow 0$ limit, we obtain another sum rule:

$$\int_0^\infty d\omega \frac{1}{\omega} \text{Re} \left[\frac{\sigma_{\alpha\alpha}(\omega)}{\epsilon_{\alpha\alpha}(\omega)} \right] = \frac{e^2}{2\hbar} K_{\alpha\alpha}. \quad (17)$$

Here we removed the superscript L , because the conductivity σ^L at $\mathbf{q} \rightarrow 0$ should not depend on whether the current is longitudinal or not.

Our sum rule Eq. (17), which relates the quantum weight to the conductivity and dielectric function, applies to general many-body systems. For 3D Coulomb systems, it reduces to Eq. (8). To see this, we use Eq. (6)

and Eq. (16) to relate σ^L to the dielectric function ϵ as

$$\begin{aligned} \sigma_{\alpha\beta}^L(\mathbf{q} \rightarrow 0, \omega) &= \frac{-i\omega}{U(\mathbf{q})q_\alpha q_\beta} (\epsilon(\mathbf{q}, \omega) - 1) \\ &= -i\omega\epsilon_0(\epsilon(\omega) - 1), \end{aligned} \quad (18)$$

where we have used $U(\mathbf{q}) = 1/(\epsilon_0 q^2)$ in the second equality. Plugging this into Eq. (17) recovers Eq. (8).

Eq. (18) becomes simplified when the dielectric function $\epsilon(\omega)$ at $\mathbf{q} = 0$ reduces to 1. This occurs in gapped systems with short-range interaction and in gapped Coulomb systems in reduced dimensions $d = 1, 2$, where $U(\mathbf{q})\Pi(\mathbf{q}, \omega)$ vanishes at $\mathbf{q} \rightarrow 0$. For such systems, Eq. (18) directly relates the optical conductivity to the quantum weight,

$$\int_0^\infty d\omega \frac{\text{Re} \sigma_{\alpha\alpha}(\omega)}{\omega} = \frac{e^2}{2\hbar} K_{\alpha\alpha}, \quad \text{when } \epsilon(\omega) = 1. \quad (19)$$

This sum rule relates the negative first moment of optical conductivity to the ground-state static structure factor at small \mathbf{q} , and therefore can be regarded as a generalization of the f -sum rule relating the zeroth moment of optical conductivity (i.e., optical spectral weight) to the electron density.

Quantum weight and quantum metric.— Eq. (19) is reminiscent of the SWM sum rule for insulating states [4], which relates the optical conductivity $\sigma(\omega)$ to the many-body quantum metric:

$$\int_0^\infty d\omega \frac{\text{Re} \sigma_{\alpha\alpha}(\omega)}{\omega} = \frac{\pi e^2}{\hbar} G_{\alpha\alpha}. \quad (20)$$

where the many-body quantum metric G is defined by the change of the many-body ground state under twisted boundary condition:

$$G_{\alpha\beta} \equiv \text{Re} \langle \partial_{\theta_\alpha} \Psi_\theta | (1 - P_\theta) | \partial_{\theta_\beta} \Psi_\theta \rangle_{\theta=0}, \quad (21)$$

where $|\Psi_\theta\rangle$ is the ground state satisfying the twisted boundary condition specified by θ : $\Psi_\theta(\mathbf{r}_1, \dots, \mathbf{r}_n + \mathbf{L}_\mu, \dots, \mathbf{r}_N) = e^{i\theta_\mu} \Psi_\theta(\mathbf{r}_1, \dots, \mathbf{r}_n, \dots, \mathbf{r}_N)$ with \mathbf{L}_μ the vector of system size in μ -direction, and $P_\theta = |\Psi_\theta\rangle\langle\Psi_\theta|$. $\theta = 0$ corresponds to the periodic boundary condition.

It should be clear that the many-body quantum metric and the quantum weight are conceptually distinct quantities: the former describes the quantum geometry of the ground states over twisted boundary condition, while the latter describes the density correlation in the ground state. Nonetheless, we conclude from Eqs. (19) and (20) that for systems with short-range interactions and Coulomb systems of reduced dimensions, many-body quantum metric G and quantum weight K are equal in the thermodynamic limit:

$$K = 2\pi G, \quad \text{when } \epsilon(\omega) = 1. \quad (22)$$

Note that while the quantum weight K is defined solely from a single ground state, the quantum metric G is not;

rather it is defined with the derivative of $|\Psi_\theta\rangle$ with respect to θ . Therefore, Eq. (22) is a remarkable result showing that a fundamental quantum geometric quantity is encoded in the static structure factor, and therefore can be directly measured.

One may verify the equality between K and G explicitly for noninteracting band insulators, which have $\epsilon(\omega) = 1$ due to the absence of screening. In this case, it is straightforward to show that the static structure factor for finite \mathbf{q} is given by (see Supplemental Materials for details)

$$S_{\mathbf{q}} = \int_{\text{BZ}} \frac{d^d \mathbf{k}}{(2\pi)^d} \text{Tr}[P(\mathbf{k})(P(\mathbf{k}) - P(\mathbf{k} + \mathbf{q}))], \quad (23)$$

where $P(\mathbf{k}) = \sum_n^{\text{occ}} |u_{n\mathbf{k}}\rangle \langle u_{n\mathbf{k}}|$ is the projection operator onto the occupied bands at wavevector \mathbf{k} with $|u_{n\mathbf{k}}\rangle$ the cell-periodic Bloch wavefunction for n -th band. Then, the quantum weight defined by the q^2 term in $S_{\mathbf{q}}$ is

$$K_{\mu\nu} = 2\pi \int_{\text{BZ}} \frac{d^d \mathbf{k}}{(2\pi)^d} g_{\mu\nu}(\mathbf{k}), \quad (24)$$

where $g_{\mu\nu}(\mathbf{k}) = (1/2) \text{Tr}[(\partial_\mu P(\mathbf{k}))(\partial_\nu P(\mathbf{k}))]$ is the quantum metric of the occupied Bloch bands, originally introduced in the study of Wannier functions [3]. Indeed, the integral of g over the Brillouin zone gives the many-body quantum metric of noninteracting band insulators, confirming the relation Eq. (22).

In contrast, for 3D Coulomb systems, $\epsilon(\omega)$ generally differs from 1, and therefore quantum weight and quantum metric are *unequal*. To illustrate this point, consider the example of 3D Wigner electron solid described by Eq. (2). Its quantum metric can be calculated from the SWM sum rule (20) using (9) and (18):

$$G = \frac{\hbar\epsilon_0 \omega_p^2}{2e^2 \omega^T}. \quad (25)$$

Comparison with the expression for the quantum weight (4) shows $K \neq 2\pi G$ because longitudinal and transverse modes have different frequencies at $\mathbf{q} \rightarrow 0$, $\omega^L \neq \omega^T$ —a consequence of the long-range Coulomb interaction in three dimensions.

It is worth adding that upper and lower bounds on the quantum metric G can also be obtained from sum rules as we did for the quantum weight. Specifically, by considering the zero-th, negative-first and negative-second moments for optical conductivity $\text{Re} \sigma(\omega) = -\omega \text{Im} \epsilon(\omega)$ [6, 13], it can be shown that

$$\pi(\epsilon - 1)E_o \leq e^2(2\pi G)/\epsilon_0 \leq \pi\sqrt{\epsilon - 1}\hbar\omega_p \leq \frac{\pi(\hbar\omega_p)^2}{E_o}. \quad (26)$$

where E_o is the optical gap, i.e., the energy of the lowest optical excitation (rather than the plasmon energy). We note that the upper bound in terms of the spectral weight

and optical gap was derived in Ref. [4] and compared to the calculated quantum metric for real materials in Ref. [14]. Recently, the tighter upper bound in terms of the spectral weight and static dielectric constant was independently found in Refs. [15, 16], using the Cauchy-Schwartz inequality. The lower bound in terms of the optical gap and the static dielectric constant was derived in an earlier version of this work [17]; see also related discussions in Refs. [18, 19].

We also calculate the bounds on the quantum metric for real materials and the results are given in Supplemental Materials. For the materials with a large optical gap, the bounds constrain the value of the quantum metric to a quite narrow range. For example, in cubic boron nitride (c-BN), the quantum metric is bounded as $0.87 \text{ \AA}^{-1} \leq 2\pi G \leq 1.21 \text{ \AA}^{-1}$. The bounds also work well for some ionic crystals: for example, the bound for NaCl is $0.18 \text{ \AA}^{-1} \leq 2\pi G \leq 0.59 \text{ \AA}^{-1}$.

Discussion.— To summarize, by considering the static structure factor at small wavevector, we introduced the general concept of quantum weight for many-body systems with a conserved $U(1)$ charge. Interestingly, besides describing long-wavelength charge fluctuations, the quantum weight is intimately related by sum rules to plasmon excitations in 3D Coulomb systems, and to the optical conductivity in gapped systems with short-range interactions or in reduced dimensions.

Our study of quantum weight in relation to charge fluctuation also complements early study of many-body quantum metric in relation to polarization fluctuation described by the second moment of electron's center of mass position. The seminal work by SWM [4] first explored the relation between polarization fluctuation and the many-body quantum metric. Later, in an insightful work [5], Resta showed that polarization fluctuation depends on the boundary condition, and for 3D systems with long-range Coulomb interaction, the SWM relation holds only for the “purely transverse” boundary condition. The subtlety with regard to polarization fluctuation is due to the fact that the position operator is not well defined for systems with periodic boundary condition.

Instead of polarization fluctuation, our work studies long-wavelength density fluctuation described by the static structure factor $S_{\mathbf{q}}$, which is a well-defined quantity in the thermodynamic limit and a physical observable. This allows us to relate the quantum weight to dielectric function and optical conductivity using sum rules for general systems (see Eqs. (7) and (17)). While the quantum weight and the many-body quantum metric are *different* in general, we also establish when they become equal.

Our work opens interesting directions for future study. Studying quantum weight in topological states of matter [13] and near metal-insulator transition [18] will be rewarding. It is also worth to explore the relation between quantum weight and quantum entanglement.

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Supplemental Materials

Structure factor for strongly localized electrons

Here, we calculate the structure factor for the strongly localized electrons described in the main text. The effective Lagrangian is given by [6]

$$\mathcal{L} = \sum_{\mathbf{q}} \frac{m}{2} \left(|\dot{\mathbf{u}}_{\mathbf{q}}|^2 - (\omega_0^2 + \omega_p^2 \frac{q_\alpha q_\beta}{q^2}) u_{\mathbf{q}\alpha} u_{-\mathbf{q}\beta} \right), \quad (27)$$

where $\mathbf{u}_{\mathbf{q}} = (1/\sqrt{V}) \sum_{\mathbf{R}_i} e^{-i\mathbf{q}\cdot\mathbf{R}_i} \mathbf{u}_i$ is the Fourier transform of the displacement of the i th electron \mathbf{u}_i from the equilibrium position \mathbf{R}_i .

The number density operator $n(\mathbf{r})$ is given by $n(\mathbf{r}) = \sum_i \delta(\mathbf{r} - (\mathbf{R}_i + \mathbf{u}_i))$ and thus its Fourier transform $n_{\mathbf{q}}$ is given by

$$n_{\mathbf{q}} = \int d\mathbf{r} e^{-i\mathbf{q}\cdot\mathbf{r}} n(\mathbf{r}) = \sum_i e^{-i\mathbf{q}\cdot(\mathbf{R}_i + \mathbf{u}_i)} \quad (28)$$

Therefore, for finite \mathbf{q} with the expectation value $\langle n_{\mathbf{q}} \rangle = 0$, the static structure factor is given by

$$S_{\mathbf{q}} \equiv \frac{1}{V} \langle n_{\mathbf{q}} n_{-\mathbf{q}} \rangle = \frac{1}{V} \sum_{i,j} e^{-i\mathbf{q}\cdot(\mathbf{R}_i - \mathbf{R}_j)} \langle e^{-i\mathbf{q}\cdot\mathbf{u}_i} e^{i\mathbf{q}\cdot\mathbf{u}_j} \rangle \simeq \frac{1}{V} \sum_{i,j} e^{-i\mathbf{q}\cdot(\mathbf{R}_i - \mathbf{R}_j)} \langle (\mathbf{q} \cdot \mathbf{u}_i)(\mathbf{q} \cdot \mathbf{u}_j) \rangle + \mathcal{O}(q^3) \quad (29)$$

$$= n \langle (\mathbf{q} \cdot \mathbf{u}_{\mathbf{q}})(\mathbf{q} \cdot \mathbf{u}_{-\mathbf{q}}) \rangle + \mathcal{O}(q^3). \quad (30)$$

This is Eq. (3) in the main text.

Structure factor for noninteracting band insulators

Here we calculate the static structure factor for general noninteracting band insulators. Writing the cell-periodic Bloch wavefunction for n th band as $|u_{n\mathbf{k}}\rangle$ with the wavevector \mathbf{k} , the number density operator with wavevector \mathbf{q} is given by

$$n_{\mathbf{q}} = \sum_{n,m} \sum_{\mathbf{k}} \langle u_{n,\mathbf{k}} | u_{m,\mathbf{k}+\mathbf{q}} \rangle c_{n\mathbf{k}}^\dagger c_{m,\mathbf{k}+\mathbf{q}}, \quad (31)$$

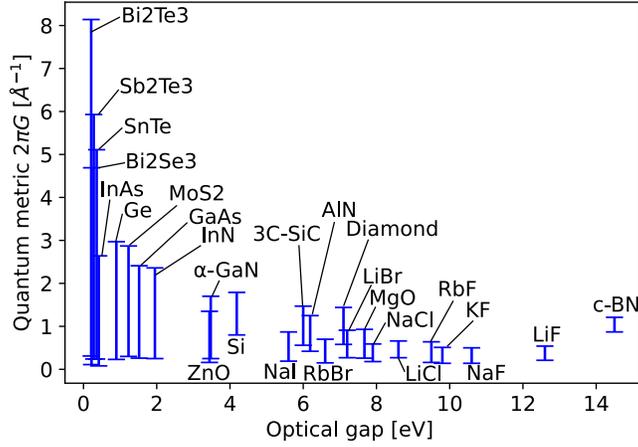


FIG. 2. The bound on the many-body quantum metric $2\pi G$ for real materials. As the energy gap, we used the optical gap obtained from optical measurement. For the details of the used parameters, see table I and Ref. [6].

with $c_{n,\mathbf{k}}$ the annihilation (creation) operator of electron in n th band with wavevector \mathbf{k} . Then the static structure factor for finite \mathbf{q} is given by

$$S_{\mathbf{q}} \equiv \frac{1}{V} \langle n_{\mathbf{q}} n_{-\mathbf{q}} \rangle = \frac{1}{V} \sum_{n,m,\mathbf{k}} \sum_{n',m',\mathbf{k}'} \langle u_{n,\mathbf{k}} | u_{m,\mathbf{k}+\mathbf{q}} \rangle \langle u_{n',\mathbf{k}'} | u_{m',\mathbf{k}'+\mathbf{q}'} \rangle \langle c_{n\mathbf{k}}^\dagger c_{m,\mathbf{k}+\mathbf{q}} c_{n'\mathbf{k}'}^\dagger c_{m',\mathbf{k}'+\mathbf{q}'} \rangle \quad (32)$$

$$= \frac{1}{V} \sum_{n,m,\mathbf{k}} \langle u_{n,\mathbf{k}} | u_{m,\mathbf{k}+\mathbf{q}} \rangle \langle u_{m,\mathbf{k}+\mathbf{q}} | u_{n,\mathbf{k}} \rangle (1 - f_m(\mathbf{k} + \mathbf{q})) f_n(\mathbf{k}) \quad (33)$$

where $f_n(\mathbf{k}) = \langle c_{n\mathbf{k}}^\dagger c_{n\mathbf{k}} \rangle$ is the occupation number of n th band at wavevector \mathbf{k} . Defining the projection operator $P(\mathbf{k}) = \sum_n^{\text{occ}} |u_{n\mathbf{k}}\rangle f_n(\mathbf{k}) \langle u_{n\mathbf{k}}|$, we obtain an expression for $S_{\mathbf{q}}$ for a general noninteracting system as

$$S_{\mathbf{q}} = \frac{1}{V} \sum_{\mathbf{k}} \text{Tr}[P(\mathbf{k})(1 - P(\mathbf{k} + \mathbf{q}))] = \frac{1}{V} \sum_{\mathbf{k}} \text{Tr}[P(\mathbf{k})(P(\mathbf{k}) - P(\mathbf{k} + \mathbf{q}))] \quad (34)$$

where we have used $P(\mathbf{k})^2 = P(\mathbf{k})$ in the last equality. Further rewriting the summation over \mathbf{k} with integral, we obtain:

$$S_{\mathbf{q}} = \int_{\text{BZ}} \frac{d^d \mathbf{k}}{(2\pi)^d} \text{Tr}[P(\mathbf{k})(P(\mathbf{k}) - P(\mathbf{k} + \mathbf{q}))]. \quad (35)$$

In particular, for band insulators, the projection operator becomes $P(\mathbf{k}) = \sum_n^{\text{occ}} |u_{n\mathbf{k}}\rangle \langle u_{n\mathbf{k}}|$ and Eq. (35) reduces to Eq. (23) in the main text.

Figure and table for the experimental parameters

Material	$\epsilon(\infty)$	n [10^{30}m^{-3}]	E_g^T [eV]	$E_g^{T,m}$ [eV]	$E_g^T/E_g^{T,m}$	E_g^L [eV]	$E_g^{L,m}$ [eV]	$E_g^L/E_g^{L,m}$	Comment
c-BN	4.46 [20]	1.02 [21]	14.5 [21]	20.11	0.721	30.4 [22]	42.48	0.716	E_g^T is direct gap.
Si	12.0 [21]	0.700 [21]	4.18 [21]	9.38	0.446	16.7 [23]	32.44	0.515	E_g^T is direct gap.
Diamond	5.7 [21]	1.06 [21]	7.1 [24]	17.62	0.403	34.0 [25]	42.06	0.808	E_g^T is direct gap.
LiCl	2.78 [26]	0.589[27]	8.6 [28]	21.36	0.403	-	35.62	-	E_g^T is from the lowest absorption peak
LiF	1.96 [26]	0.739[27]	12.6 [29]	32.58	0.387	-	45.61	-	E_g^T is an excitonic gap
3C-SiC	6.38 [21]	0.965 [21]	6.0 [21]	15.73	0.381	21.8 [30]	39.73	0.549	E_g^T is direct gap.
AlN	4.93 [21]	0.958 [21]	6.19 [21]	18.34	0.338	-	40.72	-	E_g^T is direct gap.. $\epsilon(\infty) = \epsilon_{\parallel}(\infty)$
NaCl	2.34 [26]	0.624 [31]	7.9 [28]	25.34	0.312	15.5 [23]	38.77	0.400	E_g^T is from the lowest absorption peak
KCl	2.19 [26]	0.578 [31]	7.8 [28]	25.87	0.301	14.1 [32]	38.29	0.368	E_g^T is from the lowest absorption peak. E_g^L is the first prominent peak in EELS
LiBr	3.17 [26]	0.914[27]	7.2 [28]	24.09	0.299	-	42.90	-	E_g^T is from the lowest absorption peak
KF	1.85 [26]	0.736[27]	9.8 [28]	34.54	0.284	-	46.98	-	E_g^T is from the lowest absorption peak
MgO	2.94 [21]	1.07 [21]	7.67 [21]	27.52	0.279	22.3 [23]	47.21	0.472	E_g^T is an excitonic gap
NaF	1.74 [26]	0.804 [31]	10.6 [28]	38.70	0.274	-	51.05	-	E_g^T is from the lowest absorption peak
RbF	1.96 [26]	1.03[27]	9.5 [28]	38.38	0.248	-	53.73	-	E_g^T is from the lowest absorption peak
NaBr	2.59 [26]	0.869[27]	6.7 [28]	27.45	0.244	-	44.18	-	E_g^T is from the lowest absorption peak
KBr	2.34 [26]	0.758[27]	6.7 [28]	27.93	0.240	13.2 [32]	42.73	0.309	E_g^T is from the lowest absorption peak. E_g^L is the first prominent peak in EELS
KI	2.62 [26]	0.818[27]	5.8 [28]	26.39	0.220	11.8 [32]	42.72	0.276	E_g^T is from the lowest absorption peak. E_g^L is the first prominent peak in EELS
RbBr	2.34 [26]	0.892[27]	6.6 [28]	30.30	0.218	-	46.35	-	E_g^T is from the lowest absorption peak
NaI	2.93 [26]	0.950[27]	5.6 [28]	26.05	0.215	-	44.58	-	E_g^T is from the lowest absorption peak
RbI	2.59 [26]	0.918[27]	5.7 [28]	28.21	0.202	-	45.40	-	E_g^T is from the lowest absorption peak
α -GaN	5.2 [21]	1.66 [21]	3.48 [21]	23.36	0.149	-	53.27	-	E_g^T is A-exciton. $\epsilon(\infty) = \epsilon_{\perp}(\infty)$.
ZnO	3.75 [21]	1.60 [21]	3.44 [21]	28.30	0.122	18.2 [33]	54.81	0.332	$\epsilon(\infty) = \epsilon_{\parallel}(\infty)$.
GaAs	10.9 [21]	1.42 [21]	1.52 [21]	14.08	0.108	15.8 [34]	46.38	0.341	E_g^T is direct gap.
InN	8.4 [21]	1.80 [21]	1.95 [21]	18.34	0.106	-	53.15	-	E_g^T is direct gap.
Ge	16.0 [21]	1.41 [21]	0.898 [21]	11.40	0.079	16.0 [35]	45.59	0.351	E_g^T is direct gap.
SnTe	40 [36, 37]	1.61 [21]	0.36 [21]	7.55	0.048	-	47.75	-	E_g^T is direct gap. $\epsilon(\infty)$ varies among Ref. [36, 37] around 40-50.
Sb ₂ Te ₃	51.0 [21]	1.69 [21]	0.28 [21]	6.83	0.041	-	48.75	-	E_g^T is direct gap. $\epsilon(\infty) = \epsilon_{\perp}(\infty)$.
Bi ₂ Te ₃	85.0 [21]	1.90 [21]	0.21 [38]	5.58	0.038	-	51.49	-	$\epsilon(\infty) = \epsilon_{\perp}(\infty)$.
InAs	12.4 [21]	1.48 [21]	0.418 [21]	13.37	0.031	13.9 [39]	47.04	0.295	E_g^T is direct gap.
Bi ₂ Se ₃	29.0 [21]	1.89 [21]	0.22 [40]	9.65	0.023	-	51.98	-	$\epsilon(\infty) = \epsilon_{\perp}(\infty)$.
Li	-	0.139 [31]	-	-	-	7.0 [41]	13.84	0.506	Metal
Be	-	0.493 [31]	-	-	-	18.7 [42]	26.08	0.717	Metal
Na	-	0.276 [31]	-	-	-	19.6 [42]	26.08	0.291	Metal
Mg	-	0.516 [31]	-	-	-	10.3 [42]	26.68	0.386	Metal

TABLE I. Parameters used to calculate the gap bound in Fig. 1. $\epsilon(\infty)$ is the optical dielectric constant, n is the electron density, E_g^T is the optical gap, E_g^L is the measured plasma frequency in electron energy loss spectroscopy (EELS), and $E_g^{T/L,m}$ is the gap bound calculated following Ref. [6].